



# 17th RD50 Workshop (CERN)

## Wednesday 17 November 2010

### Defect and Material Characterization - 503/1-001 - Council Chamber (13:50 - 17:00)

-Conveners: Mara Bruzzi

time	[id] title	presenter
13:50	[8] Optical studies of defect centers formed in MCz-Si and FZ-Si by high-fluence neutron irradiation	SURMA, Barbara
14:10	[11] New results on the annealing behaviour of the E4/E5-defect	JUNKES, Alexandra
14:30	[13] TCAD simulation of Si crystal with different clusters.	Prof. VAITKUS, Juozas
14:50	[12] Properties of a new series of Hamamatsu Si diodes	Prof. VAITKUS, Juozas
15:10	[1] Annealing Effects on Depletion Voltage and Capacitance of Float Zone and Magnetic Czochralski Silicon Diodes After 800 MeV Proton Exposure	Dr TOMS, Konstantin
15:30	Coffee Break	
16:00	[25] Reverse current of heavily irradiated silicon detectors operated in the avalanche mode	EREMIN, Vladimir
16:20	[20] Discussion on Defect and Material Characterization and Pad Detector Characterization	FRETWURST, Eckhart Prof. BRUZZI, Mara